



100V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C (Note 9)
100V	8.8mΩ @ V _G S = 10V	100A
1007	11.5mΩ @ V _{GS} = 6V	100A

Description

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP.

Applications

- Motor controls
- DC-DC converters
- Power managements

Features

- Rated to +175°C Ideal for High Ambient Temperature Environm-
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes On-State Losses
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH10H010SPSQ is suitable for automotive applications requiring specific change control; This part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

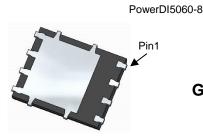
Mechanical Data

- Package: PowerDI®5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208@3
- Weight: 0.097 grams (Approximate)

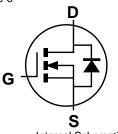
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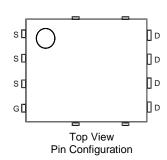
Top View



Bottom View



Internal Schematic



Site2:

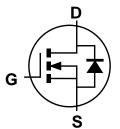
PowerDI5060-8/SWP (Type UX)



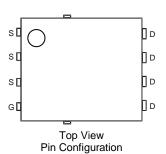
Top View



Bottom View



Internal Schematic



Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 9. Package limited.

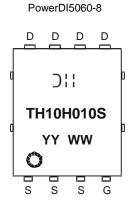


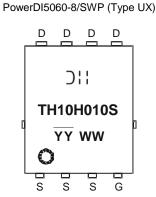
Ordering Information (Note 4)

Part Number	Package	Packing		
Fait Nullipel	Fackage	Qty.	Carrier	
DMTH10H010SPSQ-13	PowerDI5060-8	2,500	Tape & Reel	
DMTH10H010SPSQ-13	PowerDI5060-8/SWP (Type UX)	2,500	Tape & Reel	

Note:

Marking Information





TH10H010S = Product Type Marking Code

YYWW or YYWW = Date Code Marking

YY or YY = Last Two Digits of Year (ex: 23 = 2023)

WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		VDSS	100	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 5)	$T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$	lD	15 11	А
Continuous Drain Current, V _{GS} = 10V (Note 6)	$T_{C} = +25^{\circ}C$ (Note 9) $T_{C} = +100^{\circ}C$	I _D	100 87	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	Ірм	250	Α	
Maximum Continuous Body Diode Forward Current		Is	100	Α
Avalanche Current, L = 0.3mH		I _{AS}	25	Α
Avalanche Energy, L = 0.3mH		Eas	93.7	mJ
Avalanche Current (Note 7), L = 3mH		I _{AS}	14.3	Α
Avalanche Energy (Note 7), L = 3mH		Eas	307	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	3	W
Thermal Resistance, Junction to Ambient (Note 5)		Reja	49	°C/W
Total Power Dissipation (Note 6)	T _C = +25°C	PD	166	W
Thermal Resistance, Junction to Case (Note 6)		R ₀ JC	0.9	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

- 6. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 7. Guaranteed by design. Not subject to product testing.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Package limited.

^{4.} For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BVDSS	100			V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 80V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	Vgs(th)	2		4	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	Descous		6.6	8.8	mΩ	$V_{GS} = 10V, I_{D} = 13A$	
Static Dialif-Source Off-Resistance	RDS(ON)	_	8.5	11.5	11177	$V_{GS} = 6V, I_D = 13A$	
Diode Forward Voltage	VsD	_	0.8	1.3	V	Vgs = 0V, Is = 13A	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	Ciss		4468			$V_{DS} = 50V$, $V_{GS} = 0V$ f = 1MHz	
Output Capacitance	Coss	_	746	_	pF		
Reverse Transfer Capacitance	Crss	_	32	_			
Gate Resistance	Rg	_	0.91	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	_	56.4	_		V 50V L 40A	
Gate-Source Charge	Qgs	_	15.4	_	nC	$V_{DD} = 50V, I_D = 13A,$ $V_{GS} = 10V$	
Gate-Drain Charge	Qgd		14				
Turn-On Delay Time	tD(ON)	_	18.6	_			
Turn-On Rise Time	tR	_	22.5	_	ns	$V_{DD} = 50V, V_{GS} = 10V, \\ I_D = 13A, R_g = 6\Omega$	
Turn-Off Delay Time	t _{D(OFF)}	_	44.8	_			
Turn-Off Fall Time	tF	_	29.5	_			
Reverse Recovery Time	trr		54.5		ns	100 11/14 1000/	
Reverse Recovery Charge	Q _{RR}	_	106.4	_	nC	I _F = 13A, di/dt = 100A/μs	

Notes:

^{7.} Guaranteed by design. Not subject to product testing. 8. Short duration pulse test used to minimize self-heating effect.





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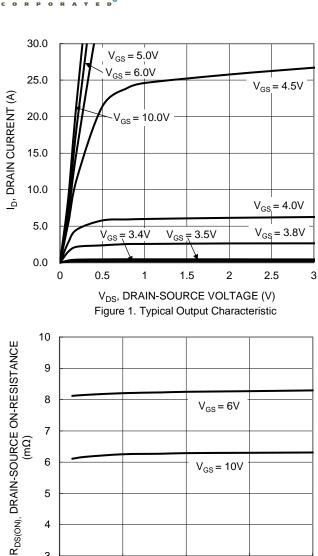
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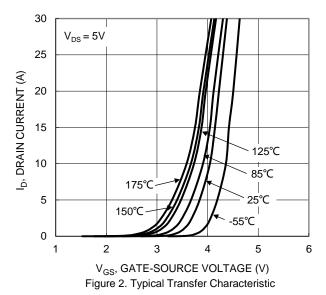
 $V_{GS} = 10V$

15

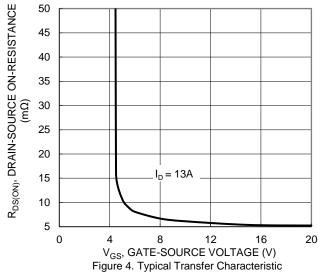
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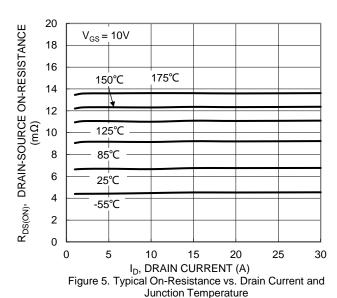
 I_D , DRAIN-SOURCE CURRENT (A)

Gate Voltage



20 Figure 3. Typical On-Resistance vs. Drain Current and





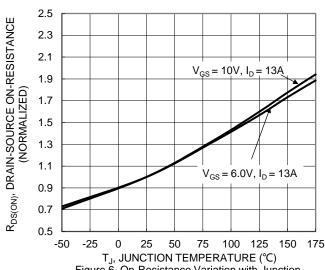
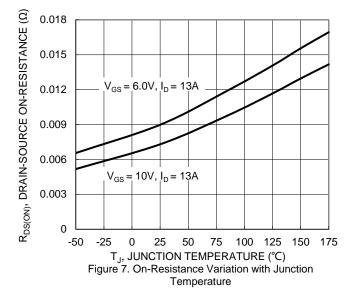
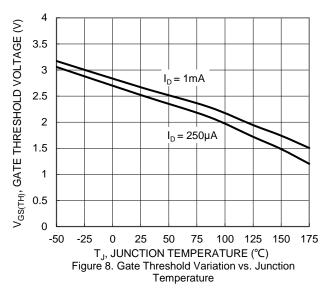


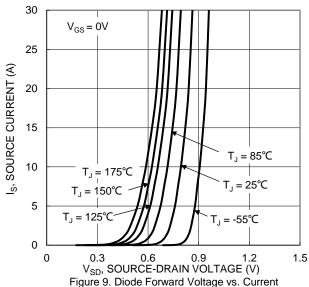
Figure 6. On-Resistance Variation with Junction Temperature

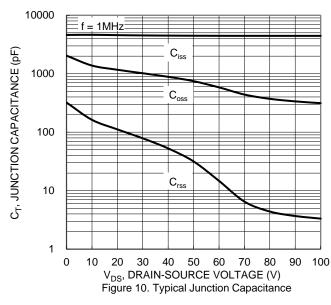


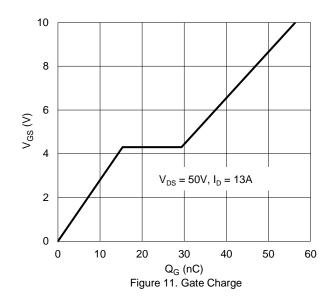


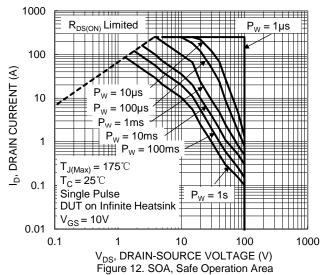














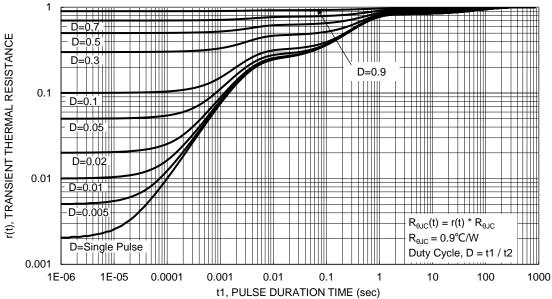


Figure 13. Transient Thermal Resistance

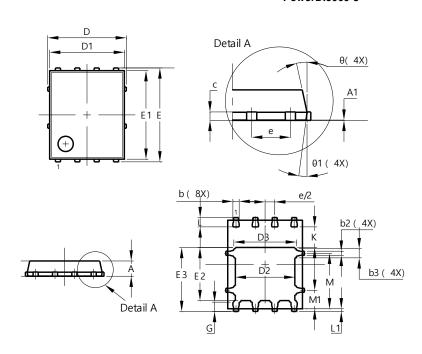


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

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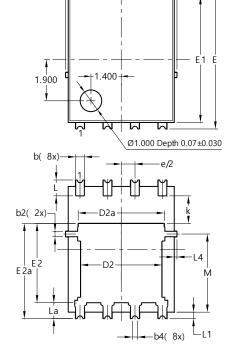
PowerDI5060-8

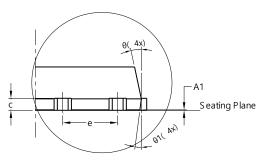


PowerDI5060-8			
Dim	Min	Max	Тур
Α	0.90	1.10	1.00
A1	0.00	0.05	-
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
C	0.230	0.330	0.277
D	ļ	5.15 BSC	;
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
Е	(6.15 BSC	;
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
е	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	-	-
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
М	3.235	4.035	3.635
M1	1.00	1.40	1.21
Θ	10°	12°	11°
Θ1	6°	8°	7°
All Dimensions in mm			

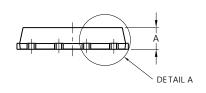
Site 2:

PowerDI5060-8/SWP (Type UX)





DETAIL A



PowerDI5060-8/SWP				
	(Type UX)			
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A1	0	0.05		
b	0.30	0.50	0.41	
b2	0.20	0.35	0.25	
b4	C).25REF		
С	0.230	0.330	0.277	
D		.15 BS(2	
D1	4.70	5.10	4.90	
D2	3.56	3.96	3.76	
D2a	3.78	4.18	3.98	
Е	6	.40 BS0)	
E1	5.60	6.00	5.80	
E2	3.46	3.86	3.66	
E2a	4.195	4.595	4.395	
е	1	.27BSC)	
k	1.05			
L	0.635	0.835	0.735	
La	0.635	0.835	0.735	
L1	0.200	0.400	0.300	
L1a	0.050REF			
L4	0.025	0.225	0.125	
М	3.205	4.005	3.605	
θ	10°	12°	11°	
θ1	6°	8°	7°	
All Dimensions in mm				

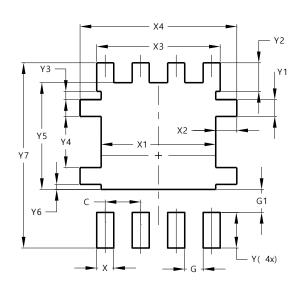


Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

Site1:

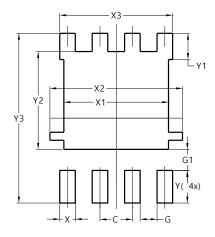
PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	0.755
Х3	4.420
X4	5.610
Υ	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y 7	6.610

Site 2:

PowerDI5060-8/SWP (Type UX)



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	5.190
Х3	4.420
Υ	1.270
Y1	1.020
Y2	3.810
Y3	6.610



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